Total	No.	of Qu	estions: 09]	200	SEAT No.:				
P-9067					 [Total No	o. of Pages : 4			
			17	1701 2					
			[6	178] - 2					
	F.E.								
ENGINEERING PHYSICS									
(2019 Pattern) (Semester - I/II) (107002)									
Time	: 21/2	Hou	rs]		[Max	. <i>Marks</i> : 70			
Instru	ıctioı	ns to	the candidates:						
	1)	Q. Q	1 is compulsory, Answer (Q2 or Q3, Q4 or	Q5, Q6 or Q7, Q8 or	<i>Q9</i> .			
	2)	Nea	t diagrams must be drawn	wherever necess	sary.	^			
	3)	Figi	ires to the right indicates	full marks.		1.			
	<i>4)</i>		of Electronic pocket calc						
	<i>5)</i>	Assi	ume suitable data, if neces	sary.	35				
Physi	cal C	Sonst	ints:-	0	2				
1 nysi	•		nk's constant h = 6.63 × 10	0 ⁻³⁴ J.S	2				
• Mass of electron $m_e = 9.1 \times 10^{-31} \text{ Kg}$									
	• Charge on election $e = 1.6 \times 10^{-19} \text{ C}$								
				D/A					
Q 1)	Wr	ite th	e correct option with a	nswer for the fo	ollowing (1 mark e	ach). [10]			
	i)		de Broglie wavelengtl		ortional to mass of	the particle			
		and							
		a)	Directly, directly	•	Inversely, inversely	,			
		c)	Directly, inversely	· · · · · · · · · · · · · · · · · · ·	Inversely, directly	V			
-	ii)		wave function is finite,	single valued,	continuous and nor	malizable it			
	フ		alled as	1.\	D 1 1:000 000				
		a)	Well behaved function	· · · · · · · · · · · · · · · · · · ·	Probability function	1,			
		c)	Fermi function	,	None of these				
	iii)		senberg Uncertainty Pr momentum	rinciple is the	product of	in position			
		a)	Difference	b)	Uncertainties				
		c)	Addition	d)	Subtraction				
				200	•	<i>P.T.O.</i>			

	iv)		In Hall effect, when a specimen caring current I is placed in transverse magnetic field B then electric field developed in specimen is				
		to I and B					
		a)	parallel	b)	intersect		
		c)	perpendicular	d)	none of above		
	v)	The	resistivity has unit				
		a)	Ohm-m	b)	Ohm		
		c)	Ohm/m	d)	Ohm/cm		
	vi)	Sup	erconductivity is characterized	by a	state of		
		a)	Finite resistivity	b)	Infinite resistivity		
		c)	Zero resistivity	d)	Zero conductivity		
	vii)	Sup	erconductor is a perfect	m	aterial.		
		a)	Insulator	b)	Semiconductor		
		c) Q	Dielectric	d)	Diamagnetic		
	viii)	1		attrac	ted when placed in the external		
	0	mag	metic field		Ole .		
		a)	Paramagnetic material	b)	Diamagnetic material		
		c)	Ferromagnetic materials	9)	Ferrimagnetic materials		
	ix)	A na	anoparticle has dimensions in the	ie ran	_		
		a)	10 to 100 micrometres	b)	1 to 100 nanometres,		
		c)	1 to 10 nanometres	d)	Greater than 100 nm		
	x)			te voi	ds, cracks, flaws present inside		
			material				
		a)	Destructive testing	,•			
	the material a) Destructive testing b) Both destructive and non-destructive testing c) None in destructive and non-destructive testing				re testing		
	つ)	(C)	None in destructive and non-d	estru	ctive testing		
		d)	Non-destructive testing		2, 83		
(12)	-)	D	C.1 1:	1 4 -			
Q^{2}	a)		ive Schrodinger's time Indepen				
	b)		e and explain Heisenberg's unco				
	c)		e of an electron in the rigid box		the ground state and first excited ngth ! A°. [4]		
		2 2000	OR	101			
				2			
[[15	701	•		- V			

<i>Q3</i>)	a)	Derive the equation for energy of the particle is enclosed in a one- dimensional rigid box (infinite potential well). [6]
	b)	State de Broglie hypothesis. Derive the equation of de Broglie wavelength for an electron accelerated by a potential difference "V". [5]
	c)	An electron has a speed of 600 m/s with an accuracy of 0.005 %. Find
		the uncertainty in its 4 position. [4]
Q 4)	a)	Explain classification of solids on the basis of Band Theory. [6]
	b)	Explain the working of PN junction diode in (a) forward bias (c) reverse
		bias on the basis of energy level diagram. [5]
	c)	Calculate the mobility of charge carriers in doped silicon whose
		conductivity is 100 per Ω -m and the Hall coefficient is 3.6 x 10^{-4} m ³ /
		coulomb: [4]
		OR OR
Q 5)	a)	Explain Hall effect. Derive the equation of Hall coefficient. [6]
	b)	Prove that in intrinsic semiconductor fermi level lies exactly at centre
	6	between valence band and conduction band. [5]
	c) *	Calculate the conductivity of pure silicon at room temperature when
		concentration of carriers is 1.6 x 10 ¹⁰ per cc [μ_e =1500 cm ² /V-sec,
		$\mu_{\rm h} = 500 {\rm cm}^2/{\rm V-sec}$. [4]
06)	۵)	Differentiate hatereauter I are an analyst are
<i>Q6)</i>	a)	Differentiate between type I and type II superconductors. [6]
	b)	Define the terms: [5]
		i) Magnetic field strength (H)
		ii) Magnetization (M)
		iii) Magnetic Susceptibility (χ)
	.C	iv) Magnetic Induction (B)
	~\	v) Relative Permeability (μ)
	c)	Explain DC and AC Josephson effect in brief. [4]
		OR OF SOL
Q 7)	a)	Explain how the information is recorded and retrieved in magneto-optical
	1 \	recording devices. [6]
	b)	State and Explain Meissner effect. Show that superconductors exhibit
	. `	perfect diamagnetism. [5]
	c)	Differentiate ferromagnetic materials and paramagnetic material. (Any two
		points) [4]

- **Q8)** a) Explain Electrical and Mechanical properties of nanoparticles. [6]
 - b) Differentiate between Non-Destructive Testing techniques and destructive testing techniques. [5]
 - c) Explain the applications of Nano particles in Targeted Drug Dilivery. [4]
- **Q9)** a) What is Non Destructive Testing? Explain Ultrasonic Testing Technique for flaw detection. [6]
 - b) Explain nano technology is used in, Automobile and electronics field.[5]
 - c) An ultrasonic pulse of frequency 130 kHz is sent through a block of steel. The echo pulse is recorded after 1.695 microseconds. If the velocity of ultrasonic in steel is 5900 m/s, calculate the thickness of the steel block and the wavelength of the pulse. [4]

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